

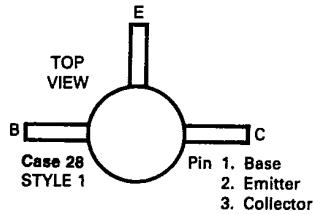
6367255 MOTOROLA SC (DIODES/OPTO)

34C 38221 D

MICRO-T (continued)

T-37-15

MMT3546 — PNP SWITCHING TRANSISTOR



- designed for high-speed, low-level switching applications, where high-density packaging is required.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CB}	15	Vdc
Emitter-Base Voltage	V_{EB}	4.5	Vdc
Collector Current — Continuous	I_C	250	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	250 2.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.50	°C/mW

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Min	Max	Unit
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OFF CHARACTERISTICS

BV_{CEO}	$I_C = 10 \text{ mAdc}, I_B = 0$	12	—	Vdc
BV_{CBO}	$I_C = 10 \mu\text{Adc}, I_E = 0$	15	—	Vdc
BV_{EBO}	$I_E = 10 \mu\text{Adc}, I_C = 0$	4.5	—	Vdc
I_{CBO}	$V_{CB} = 10 \text{ Vdc}, I_E = 0$	—	100	nAdc
I_{EBO}	$V_{EB} = 3.0 \text{ Vdc}, I_C = 0$	—	100	nAdc

ON CHARACTERISTICS

h_{FE}	$I_C = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$	30	—	—
	$I_C = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$	15	—	—
$V_{CE(sat)}$	$I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$	—	0.15	Vdc
	$I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc}$	—	0.5	Vdc
$V_{BE(sat)}$	$I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$	0.7	0.9	Vdc
	$I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc}$	—	1.6	Vdc

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continued

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MICRO-T (continued)

MMT3546 (continued)

7-37-15

DYNAMIC CHARACTERISTICS

f_T	$I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ MHz}$	700	—	MHz
C_{ob}	$V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$	—	6.0	pF
C_{ib}	$V_{BE} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$	—	8.0	pF

SWITCHING CHARACTERISTICS

t_d	$V_{CC} = 3.0 \text{ Vdc}, V_{BE} = 2.0 \text{ Vdc},$ $I_C = 50 \text{ mAdc}, I_{B1} = 5.0 \text{ mAdc}$	—	10	ns
t_r		—	15	ns
t_s	$V_{CC} = 3.0 \text{ Vdc}, I_C = 50 \text{ mAdc},$ $I_{B1} = I_{B2} = 5.0 \text{ mAdc}$	—	20	ns
t_f		—	15	ns

FIGURE 1 – DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

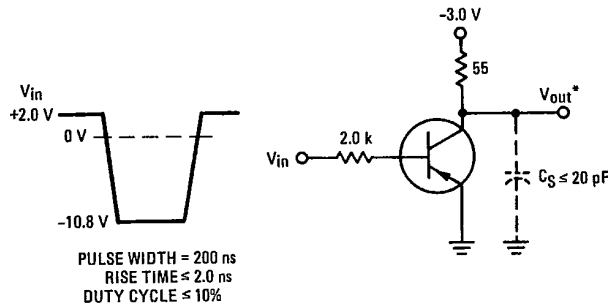
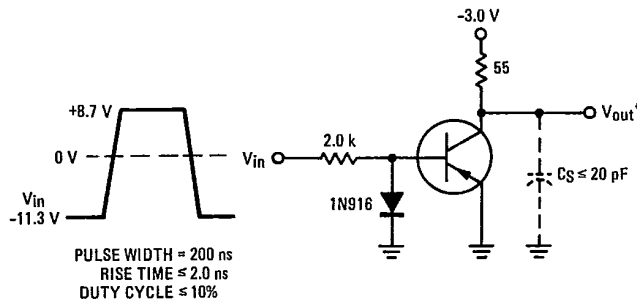


FIGURE 2 – STORAGE AND FALL TIME EQUIVALENT TEST CIRCUIT



*OSCILLOSCOPE RISE TIME ≤ 1.0 ns